

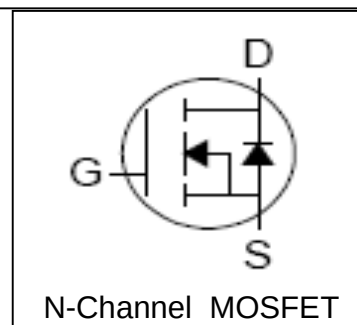
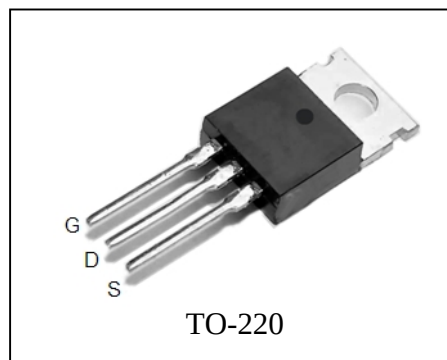
Features

- 40V/100A,
R_{DS (ON)} = 5mΩ (Typ.) @ V_{GS} = 10V
- Ultra Low On-Resistance
- Fast Switching
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free, RoHS compliant

Applications

- Switching Application Systems
- UPS

Pin Description



Absolute Maximum Ratings

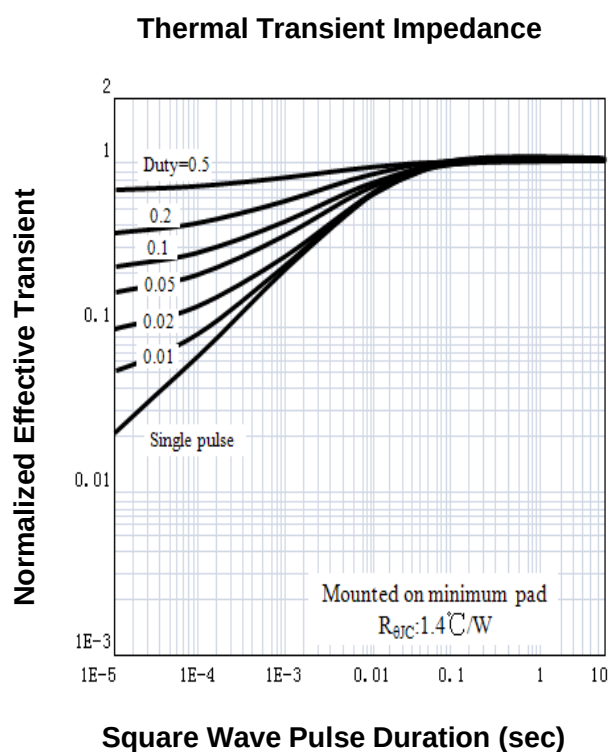
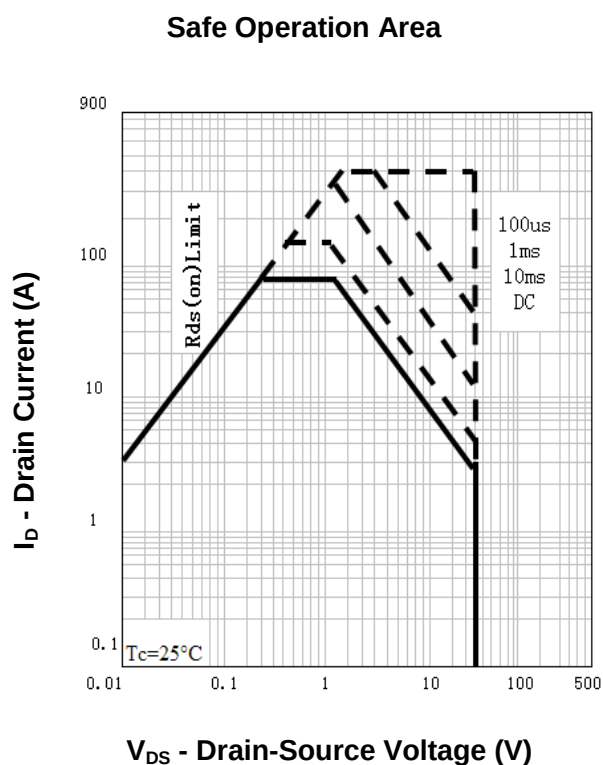
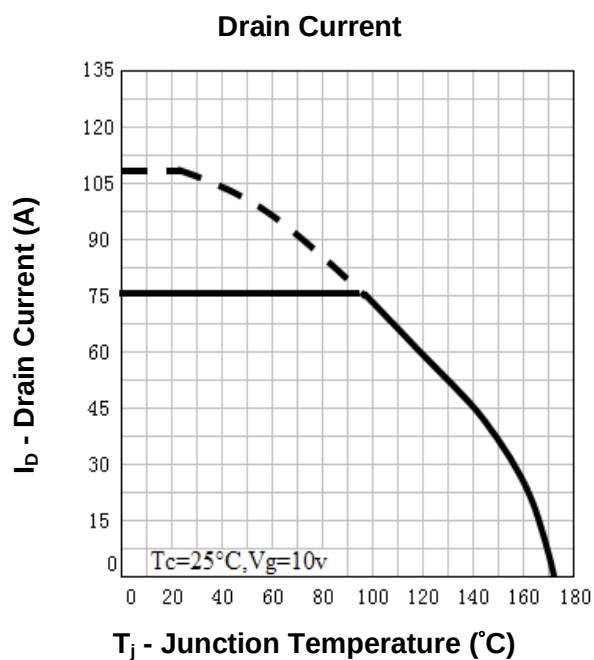
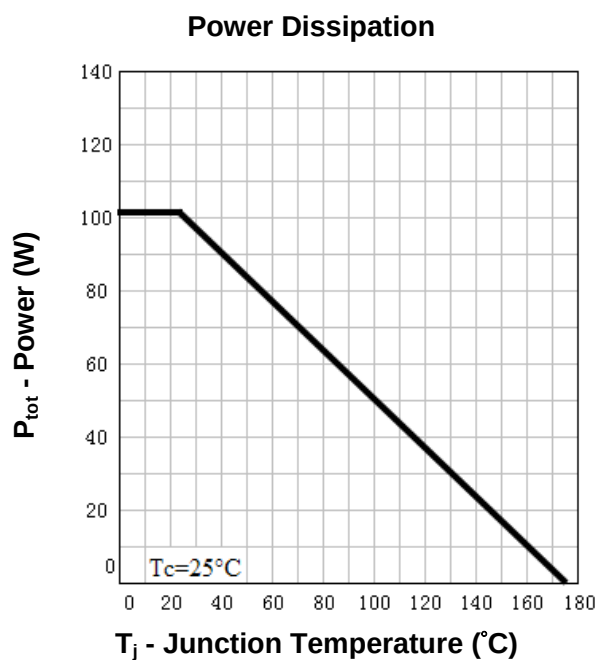
Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	100 ^①	A
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	400 ^②	A
I _D	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	100 ^①	A
		T _C =100°C	73	
P _D	Maximum Power Dissipation	T _C =25°C	107	W
		T _C =100°C	53	
R _{θJC}	Thermal Resistance-Junction to Case		1.4	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^③	Avalanche Energy, Single Pulsed		576	mJ

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU3582R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 40V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^④	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =40A		5	6.5	mΩ
Diode Characteristics						
V _{SD} ^④	Diode Forward Voltage	I _{SD} =40 A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs		24		ns
Q _{rr}	Reverse Recovery Charge			18		nC
Dynamic Characteristics ^⑤						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.8		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = 32V, Frequency=1.0MHz		2110		pF
C _{oss}	Output Capacitance			480		
C _{rss}	Reverse Transfer Capacitance			260		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, R _L =35Ω, I _{DS} =40A, V _{GEN} = 10V, R _G =4Ω		15		ns
t _r	Turn-on Rise Time			95		
t _{d(OFF)}	Turn-off Delay Time			33		
t _f	Turn-off Fall Time			28		
Gate Charge Characteristics ^⑤						
Q _g	Total Gate Charge	V _{DS} =32V, V _{GS} = 10V, I _{DS} =40A		95	120	nC
Q _{gs}	Gate-Source Charge			17		
Q _{gd}	Gate-Drain Charge			38		

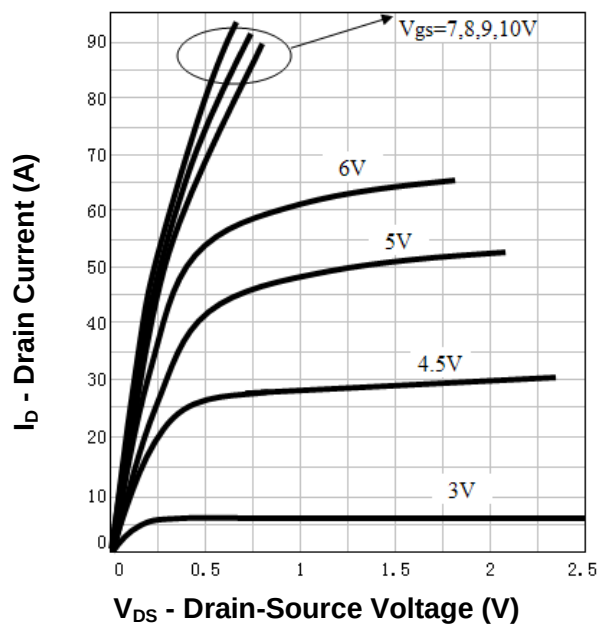
- Notes: ① Calculated continuous current based on maximum allowable junction temperature. Current limited by bond wire. Package limitation current is 75A.
 ② Pulse width limited by safe operating area.
 ③ Limited by $T_{Jmax}, I_{AS}=48A, V_{DD}=48V, R_G=47\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

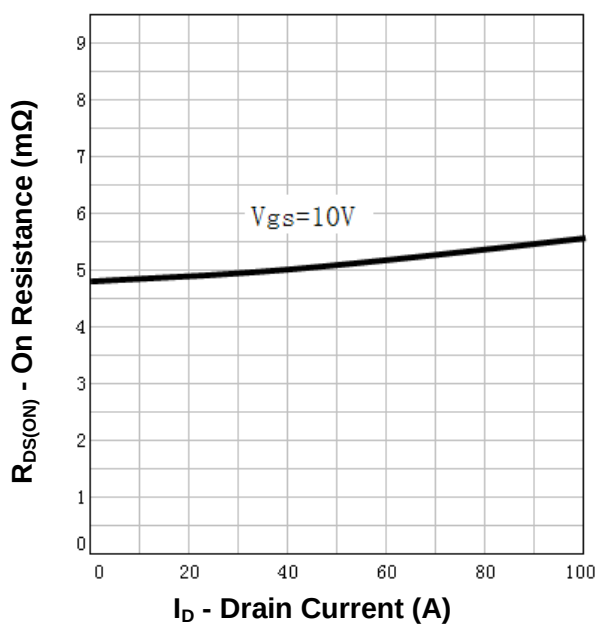


Typical Characteristics

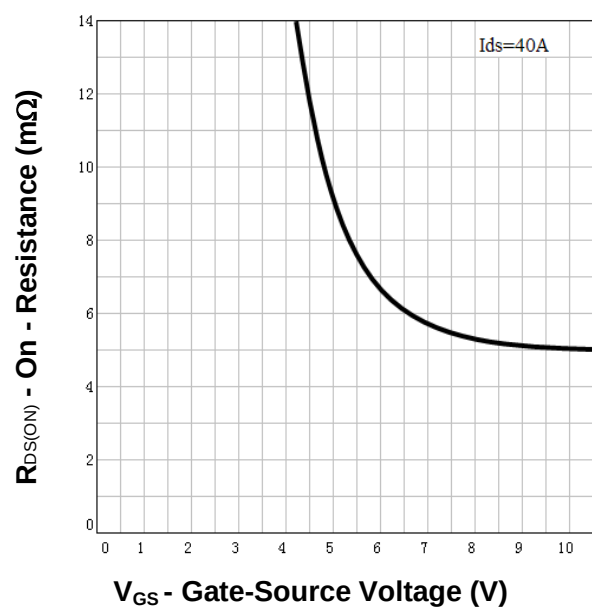
Output Characteristics



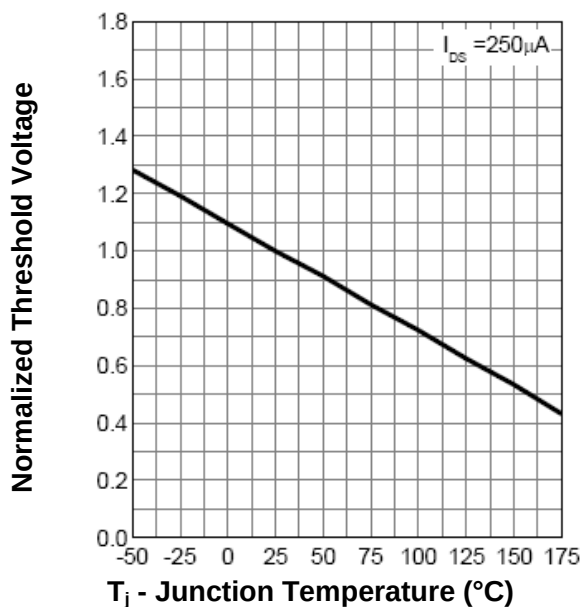
Drain-Source On Resistance



Drain-Source On Resistance

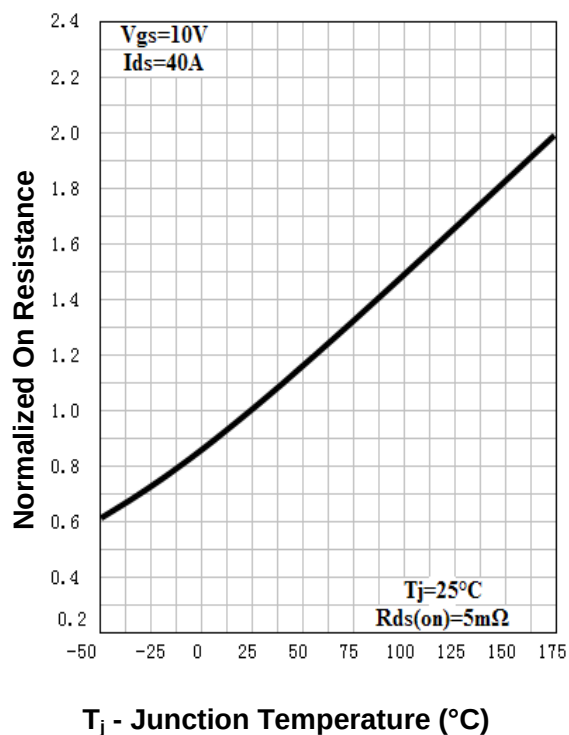


Gate Threshold Voltage

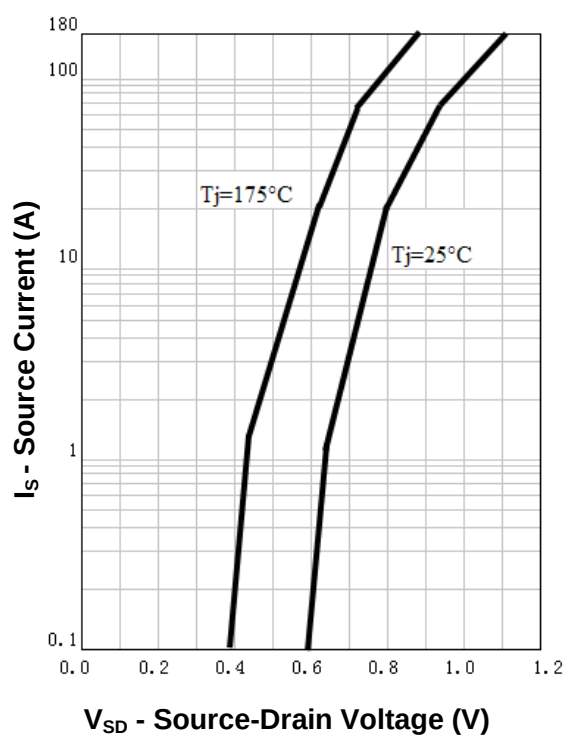


Typical Characteristics

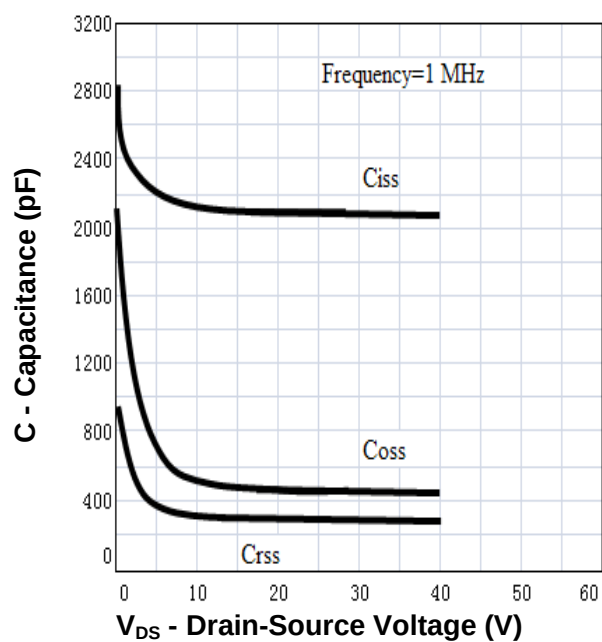
Drain-Source On Resistance



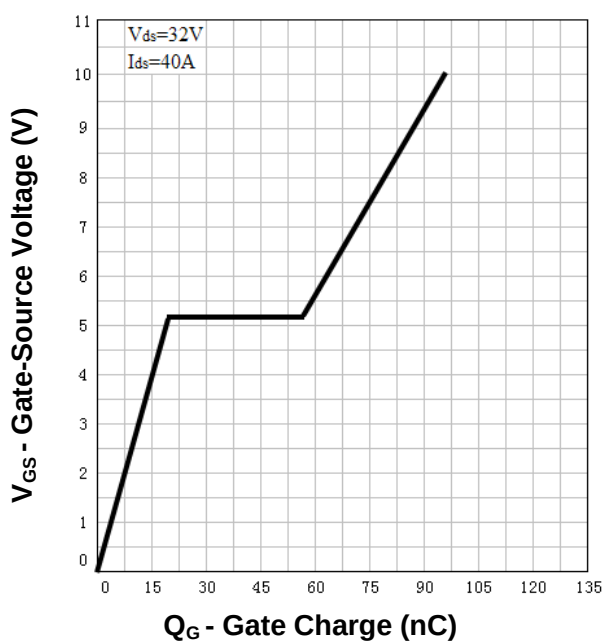
Source-Drain Diode Forward



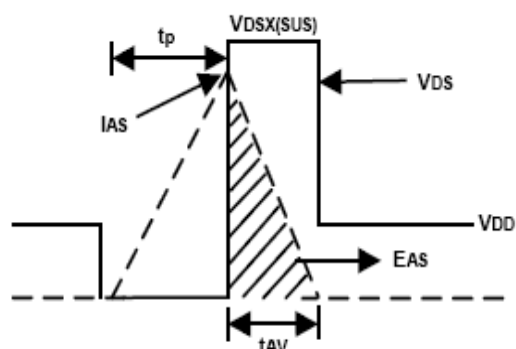
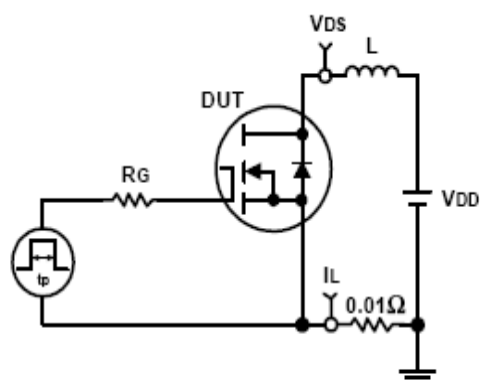
Capacitance



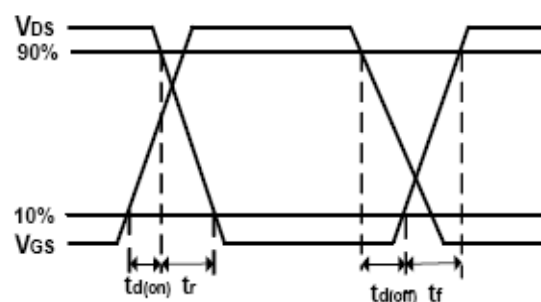
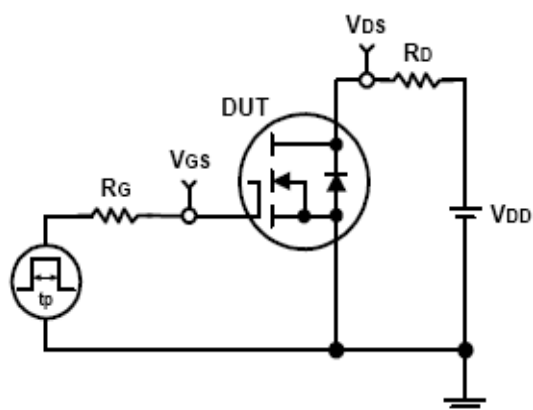
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

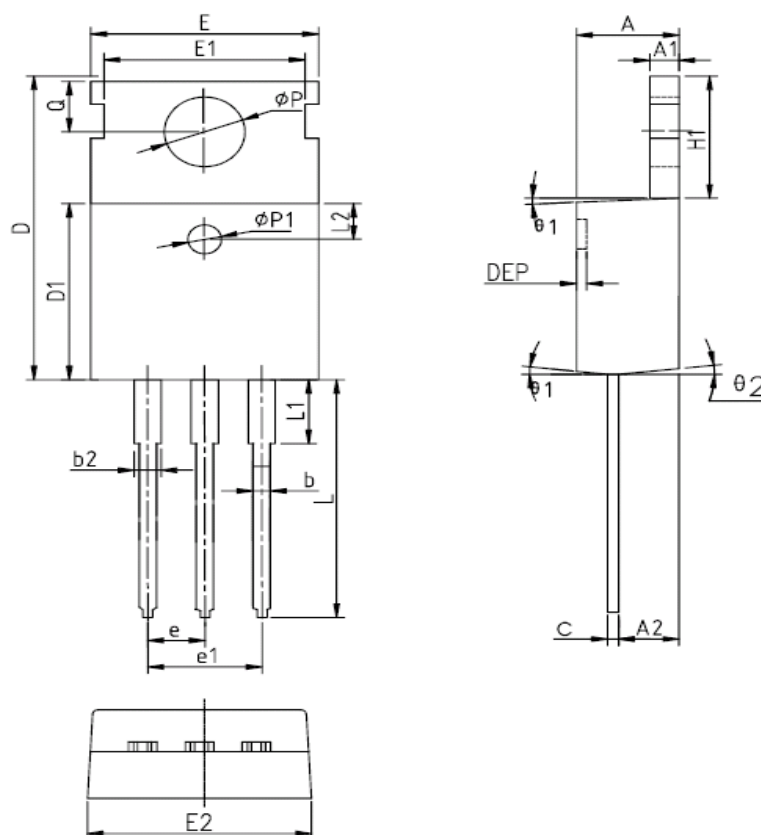


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3582R	RU3582R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	$\theta 1$	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	$\theta 2$	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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